Design And Implementation Of DMC Encoder And Decoder For Secured Applications

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Abstract

Recently memory systems have experienced significant technology developments. Error tolerance for emerging memory systems is of increasing importance. Error Correcting Codes (ECC) are frequently used for improving the reliability of a memory system. Errors are controlled in a memory system by using encoders and decoders for ECCs. ECCs do not protect from errors in the encoders and decoders. The main objective of this work is to design encoder and concurrent decoders to detect and correct errors in given pattern of input. Concurrent Error Detection (CED) employing Decimal Matrix Codes (DMC) for the syndrome generator reduces area overhead. These codes have the capability of correcting information even the transmission medium is very much susceptible for errors. Decimal Matrix codes can detect and correct errors in parallel manner. This design is implemented using Xilinx 14. 7 ISE Simulator in VHDL By using DMC codes area reduced by 13%.

Keywords: Memory Systems, Encoders and Decoders, ECC, Decimal Matrix Codes, *VHDL*

I. Introduction

Error rate is more in logic circuits. Most of the logic circuits consist of memory. From past ten years several researchers concentrated on memory cells. They designed circuits to reduce faults in memory. Even though the memory cells are protected, the error rate is not reduced to an appreciable level. Then the concentration is moved on to the surrounding circuitries of the memory to reduce error rate [1]. In most of the logic circuits at the transmitter, receiver ends encoder and decoder circuits respectively used[1]. To reduce error rate in logic circuits a fault secure encoder and decoder are needed. Single bit upset is a major concern about memory reliability, multiple cell upsets (MCUs) have become a serious reliability concern in some memory applications. In this work, novel decimal matrix code (DMC) based on divide-symbol is proposed to provide enhanced memory reliability. The proposed DMC utilizes decimal algorithm (decimal integer addition and decimal integer subtraction) to detect errors. The advantage of using decimal algorithm is that the error detection capability is maximized so that its reliability is

enhanced. Besides, the encoder-reuse technique (ERT) is proposed to minimize the area overhead of extra circuits (encoder and decoder) without disturbing the whole encoding and decoding processes, because ERT uses DMC encoder itself to be part of the decoder.

II. DMC Encoder and Decoder

DMC is used to get reliability in the presence of MCUs with reduced performance overheads. Block diagram of the proposed system used in encoder and decoder circuits is shown in Figure. 1.

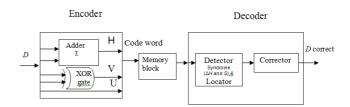


Figure 1:Block diagram of proposed DMC codes.

A. DMC Encoder

In the DMC, first, the input is divided to symbols and arrange in matrix form are performed, i. e., the N-bit word is divided into k symbols of m bits $(N = k \times m)$, and these symbols are arranged in a $k1 \times k2$ 2-D matrix ($k = k1 \times k2$, where the values of k1 and k2 represent the numbers of rows and columns in the logical matrix respectively). Second, the horizontal redundant bits H are produced by performing decimal integer addition of selected symbols per row. Here, each symbol is regarded as a decimal integer. Third, the vertical redundant bits V are obtained by binary operation among the bits per column. It should be noted that both divide-symbol and arrange-matrix are implemented in logical instead of physical. For a 32-bit word shown in Figure. 2. The cells from D0 to D31 are information bits. This 32-bit word has been divided into eight symbols of 4-bits each. k1 = 2 and k2 = 4 have been chosen simultaneously (k1=rows, k2=columns respectively). H_0 - H_{19} are horizontal check bits. V_{15} - V_0 are vertical redundant bits, and the remaining bits U_{31} -

 U_0 are the information bits which are directly copied from D_{31} - D_0 . The En is enable signal. When $k=2\times 4$ and m=4, the maximum correction capability is up to 5 bits and the number of redundant bits are 36. In order to enhance the reliability of memory, the error correction capability is considered, so $k=2\times 4$ and m=4 are utilized to construct DMC.

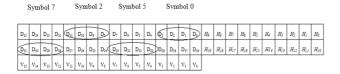


Figure 2: 32-bit DMC logical organization

The encoder that computes the redundant bits using multibit adders and XOR gates is shown in figure.

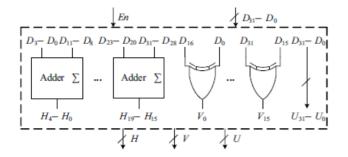


Figure 3: Encoder Structure

The horizontal redundant bits H can be obtained by decimal integer addition as follows:

$$H_4H_3H_2H_1H_0 = D_3D_2D_1D_0 + D_{11}D_{10}D_9D_8 \tag{1}$$

$$H_9H_8H_7H_6H_5 = D_7D_6D_5D_4 + D_{15}D_{14}D_{13}D_{12}$$
 (2)

$$H_{14}H_{13}H_{12}H_{11}H_{10} = D_{16}D_{17}D_{18}D_{19} + D_{24}D_{25}D_{26}D_{27}$$
 (3)

$$H_{19}H_{18}H_{17}H_{16}H_{15} = D_{20}D_{21}D_{22}D_{23} + D_{28}D_{29}D_{30}D_{31}$$
 (4)

where "+"represents decimal integer addition. For the vertical redundant bits V, we have

$$V0 = D_0 \oplus D_{16} \tag{5}$$

$$V1 = D_0 \oplus D_{17} \tag{6}$$

and similarly for the remaining vertical redundant bits.

B. Fault-Tolerant Memory

During the encoding (write) process, information bits are given to the encoder, and then the horizontal redundant bits H and vertical redundant bits V are obtained from the DMC encoder. When the encoding process is completed, the obtained DMC code word is stored in the memory. If errors

occur in the memory, errors can be corrected in the decoding (read) process[7]. Because of the advantage of decimal algorithm, the proposed system has higher fault-tolerant capability with lower performance overheads. In the fault-tolerant memory, the ERT technique is proposed to reduce the area overhead of extra circuits.

C. DMC Decoder

To obtain the corrected word decoding process is needed. The horizontal syndrome bits

 $\Delta H_4H_3H_2H_1H_0$ and the vertical syndrome bits S3-S0 can be calculated as

$$\Delta H_4 H_3 H_2 H_1 H_0 = H_4 H_3 H_2 H_1 H_0' - H_4 H_3 H_2 H_1 H_0 \tag{7}$$

$$S_0 = V_0' \oplus V_0 \tag{8}$$

and similarly for the other vertical syndrome bits, where "–" represents decimal integer subtraction. When $\Delta H_4H_3H_2H_1H_0$ and S3-S0 are equal to zero the stored code word has original information bits in symbol '0' where no errors occur. When $\Delta H_4H_3H_2H_1H_0$ and S3-S0 are nonzero, the induced errors are detected and located in symbol 0, and then these errors can be corrected by

$$D_{o\ correct} = D_0 \oplus S_0. \tag{9}$$

The proposed DMC decoder is divided to sub modules, for executing a specific task in the decoding process. Those sub modules are syndrome calculator, error locator, and error corrector. It can be observed from the Figure. 3 that the redundant bits must be recomputed from the received information bits D and compared to the original set of redundant bits in order to obtain the syndrome bits ΔH and S. Then error locator uses ΔH and S to detect and locate errors that occur in the input bits. Finally in the error corrector, these errors can be corrected by inverting the values of error bits.

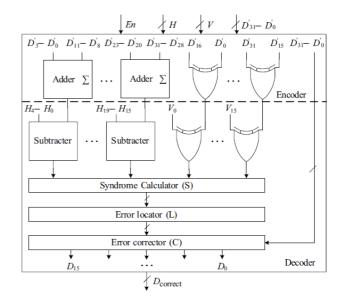


Figure 4: Decoder structure using ERT

In the proposed system area of DMC is minimized by reusing its encoder. This is called the Encoder Reusing Technique (ERT).

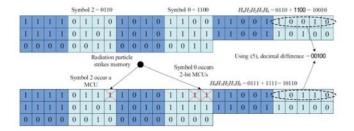


Figure 5: The process of detecting and correcting error

The ERT can reduce the area overhead of DMC without disturbing the whole encoding and decoding processes shown in figure. 4. It can be observed that the DMC encoder is also reused for obtaining the syndrome bits in DMC decoder. Therefore, the whole circuit area of DMC can be minimized as a result of using the existing circuits of encoder. The proposed decoder uses an enable signal En for deciding whether the encoder needs to be a part of the decoder or encoder. In other words, the En signal is used for distinguishing the encoder from the decoder, and it is under the control of the write and read signals in memory.

Extra circuit	En s	ignal	Function	
Extra circuit	Read signal	Write signal	runction	
Encoder	0	1	Encoding	
	1	0	Compute syndrome bits	

Figure 6: Functions of enable signal

Therefore, in the encoding (write) process, the DMC encoder is only an encoder to execute the encoding operations shown in figure. 6. However, in the decoding (read) process, this encoder is employed for computing the syndrome bits in the decoder. These clearly show how the area overhead of extra circuits can be reduced.

When the decimal algorithm is used to detect errors, these errors can be detected so that the decoding error can be avoided as shown in figure. 5. The detection procedure of decimal error detection uses the proposed structure is the horizontal redundant bits $H_4H_3H_2H_1H_0$ are obtained from the original information bits in symbols 0 and 2

•
$$H_4H_3H_2H_1H_0 = D_3D_2D_1D_0 + D_{11}D_{10}D_9D_8$$

= 1100 + 0110
= 10010.

When MCUs occur in symbol 0 and symbol 2 the bits in symbol 0 are upset to "1111" from "1100" $(D_3D_2D_1D_0=1111)$ and the bits in symbol 2 are upset to "0111" from "0110" $(D_{11}D_{10}D_9D_8=0111)$. During the decoding process, the received horizontal redundant bits $H_4H_3H_2H_1H_0$ are computed as follows:

$$H_4H_3H_2H_1H_0 = D_{11}D_{10}D_9D_8 + D_3D_2D_1D_0$$

= 0111 + 1111
= 10110.

Then, the horizontal syndrome bits $\Delta H4H3H2H1H0$ can be obtained using decimal integer subtraction

$$\Delta H_4 H_3 H_2 H_1 H_0 = H_4 H_3 H_2 H_1 H_0' - H_4 H_3 H_2 H_1 H_0$$

$$= 10110 - 10010$$

= 00100.

The decimal value of Δ $H_4H_3H_2H_1H_0$ is not "0," which represents that errors are detected and located in symbol 0 or symbol 2.

III. Reliability And Overheads Analysis

The proposed DMC has been implemented in HDL. It has superior protection level compared with other codes. This technique provides single-and double-error correction, but can also provide effective tolerance capabilities against large MCUs that exceed the performance of other codes.

A. Reliability Estimation

The reliability of system can be analyzed in terms of the mean time to failure (MTTF). It is assumed that MCUs arrive at memories following a Poisson distribution. For one word, the correctable probability R(S) after S radiation events can be given by [13].

$$R(S) = \sum_{i+j+\dots+z \le T} P_i^1 P_j^2 \dots P_z^S$$
(10)

where

T is the maximum number of errors and P is the correctable probability upon the reception of radiation event S which causes z errors.

For a memory with M words, the correctable probability J(S) after S radiation events can be given by [13].

$$J(S) = \sum_{a+b+\dots+e=S} \frac{C_M^x}{M^x} R_a^1 R_b^2 \cdots R_e^x$$
(11)

where x ($x \le S$) is the number of words affected by radiation events, C is the selection of x from M words in memory, and R represents the correctable probability when e radiation events affect x words.

Then the MTTF can be given by[13]

$$MTTF = \int_0^\infty J(t)dt.$$
 (12)

B. Overheads Analysis

The area overheads of OLS and DMC are 80% and 63% respectively. This indicates that the memory with the proposed scheme performs faster than OLS codes. However the proposed DMC decoding algorithm is quite simple so that the overheads are minimal.

IV. Simulation results

The simulation results are obtained by executing the VHDL files of encoder, detector, memory, corrector, and decoder on the simulator tool.

Fig 7, 8 and 9shows simulation results of Encoder and Decoder. In decoder simulation results for error detector and error corrector are shown. The information vector is given to the encoder block. The information is encoded and horizontal and vertical parity check bits are generated by using decimal algorithm. The output of encoder is stored in memory. The output of memory is input to the decoder. In the decoder encoded vector is detected and corrected.

Simulation output of Encoder:

Name	Value	1,999,996 ps	1,999,997 ps	1,999,998 ps	1,999,999 ps
l₄ clk	0				
▶ <table-of-contents> ip[31:0]</table-of-contents>	111101011	111	1010110101111111	1011010101100	
▶ 🖷 h[19:0]	110011010		1100110100110	0110010	
▶ ■ v[15:0]	000000110		00000011000	00011	
symbol0[3:1	1100		1100		
symbol1[3:	1111		1111		
▶ 🥷 symbol2[3:	0110		0110		
▶ 🥷 symbol3[3:i	0101		0101		
symbol4[3:1	1010		1010		
Symbol5[3:1	1010		1010		
▶ 🤻 symbol6[3:1	1111		1111		
▶ 🥷 symbol7[3:i	1111		1111		

Figure 7: Simulation results of encoder

Simulation output of Decoder:

lame	Value	continue.	1,999,991 pc	1,999,992 ps	1,999,993 ps	1,999;994 ps	1,999,995 ps
lig cx	0						
Ill wit	1						
IB ret	1						+
Pg (p(31.0)	111101011			111100001001010101	11111011010101010	•	
FC(Note and	0011			(011		
Serer .	1						
oversym0(3:0	1100				1990		
corsym1[3:0]	1111				11:1		
corsym2(3:0	0110				110		
eorsym3(3:0	0101				2000		
M hp(19:0)	110011010			150015000	001800180050		
60,029.0	110011010			150018050	01100110010		
geth(\$9:0]	000000000			00000000	303000000000		1
₩ vp(15:0)	000000110			000000	100000011		
ovp(15:0)	000000110			000000	100000011		
## delv[35:0]	000000010			0000000	\$00000015		
00(31:0)	111101010			1113040130301011	1111301103030190	0	

Figure 8: Simulation results of error detector

Name	waterpart of T	Value	بينيلين	1,999,961,96	1,999,962,06	1,999,963 ps	1,999,964 ps	1,999,965 ps
. N	vp(15:0)	000000110			000000	100000011		
- 16	999(\$50)	000000110			000000	100000011		
	delv[15:0]	0000000010			000000	100000011		
- 16	99(31.0)	111101011			111101010100101	1111101103010101	0	
- 10	dop@1:5	1111010114			1111010101001011	11111011110101111	ı	
- 10	ersymö(3:d)	1111			-	1111		
- 15	ersym1(Dis)	0000				5000		
- 16	erzym2(3:0)	0111				111		
- 14	ersym3(3:0)	0000				5000		
-	ersym4(0:0)	0000		7	-	0000		
- 4	ersym5(3:0)	0000	1			5000		
. 10	ersym6[3:0]	0000				5000		
- 16	ersym7(3:0)	0000	ii.			5000		
4	consym4(3:0)	1010	4			1010		
16	corsym5(3:0)	1010				1010		
- 14	corsym6(3:0	1111				111		
	consym7[3:0]	1111				iii		

Figure 9: Simulation results of error corrector

V. Conclusion

In this work, DMC was proposed for the reliability of memory. The DMC code utilizes decimal algorithm to detect errors, so that more errors are detected and corrected. The obtained results shows that proposed scheme reduces number of errors that occur in memory. The area reduction of DMC is 13% respectively.

VI. References

- [1] Kazuteru Namba and Fabrizio Lombardi "Concurrent error detection of binary and nonbinary OLS Parallel decoders", IEEE transactions on device and materials reliability vol. 14, no. 1, march. 2014.
- [2] P. Reviriego, S. Pontarelli, and J. A. Maestro, "Concurrent error detection for orthogonal Latin squares encoders and syndrome computation, "IEEE Trans. Very Large Scale Integr. (VLSI) Syst., vol. 21, no. 12, pp. 2334-2338, Dec. 2013.
- [3] S. Sabeen1, N. Bharathi Raja2, "Enhanced memory reliability using parity matrix code" International Journal of Scientific & Engineering Research, Volume 5, Issue 4, April-2014.
- [4] K. Namba and F. Lombardi, "Non-binary orthogonal latin square codes for a multilevel phase charge memory (PCM), " Dept. ECE, Northeastern Univ., Internal Rep., Jul. 2013.
- [5] Arijit Raychowdhury, Georgia Institute of technology, "Spin torque devices in embedded memory, model studies and design space exploration", IEEE/ACM International conference, pp. 572-575, 2013.
- [6] N. Savage, "Z-RAM takes on DRAM," IEEE Spectrum, vol. 47, no. 7, p. 18, Jul. 2010.
- [7] H. Naeimi and A. DeHon, "Fault secure encoder and decoder for nanomemory applications," IEEE Trans. Very Large Scale Integr. (VLSI) Syst., vol. 17, no. 4, pp. 473-486, Apr. 2009.
- [8] R. Naseer and J. Draper, "Parallel ouble error correcting code design to mitigate multi-bit upsets in SRAMs," in Proc. 34th Eur. Solid-State Circuits, pp. 222-225, Sep. 2008.
- [9] C. Wilkerson, H. Gao, A. R. Alameldeen, Z. Chishti, M. Khellah, and S.-L. Lu, "Trading off cache capacity for reliability to enable low voltage operation," in Proc. Annu. Int. Symp. Comput. Archit, pp. 203-214, 2008.
- [10] D. Ielmini, A. L. Lacaita, and D. Mantegazza, "Recovery and drift dynamics of resistance and threshold voltages in phase-change memories," IEEE Trans. Electron Device, vol. 54, no. 2, pp. 308-315, Feb. 2007.
- [11] G. C. Cardarilli, S. Pontarelli, M. Re, and A. Salsano, "Concurrent error detection in Reed-Solomon encoders and decoders," IEEE Trans. Very Large Scale Integr. (VLSI) Syst., vol. 15, no. 7, pp. 842-846, Jul. 2007.
- [12] M. Kund, G. Beitel, C.-U. Pinnow, T. Röhr, J. Schumann, R. Symanczyk, K.-D. Ufert, and G.

Müller, "Conductive bridging RAM (CBRAM): An emerging non-volatile memory technology scalable to sub 20 nm," in IEDM *Tech. Dig.*, pp. 754-757, 2005

[13] F. Alzahrani, and T. Chen, "On-chip TEC-QED ECC for ultra-large, single-chip memory systems," in Proc. IEEE Int. Conf. Comput Design Design, Very-Large-Scale Integr. (VLSI) Syst. Comput. Process., pp. 132-137, Oct. 1994.

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